

*AMENDMENTS TO THE SPECIFICATION*

Replace the paragraph beginning at page 27, line 9 with:

The first pulse laser beam having profile 24 shown in Fig. 20(a), as a profile of energy density, is applied. Object 9 moves in the direction indicated by arrow 71, and as a result, the first pulse laser beam scans object 9 in the direction indicated by arrow 34. Thus, as shown in Fig. 20(b), melted portion 26 is produced within amorphous silicon film 203 on the surface of object 9. Next, cooling is started to form laterally growing crystals 31 at the gradient portions on the both sides of profile 24 shown in Fig. 20(c). Then, the second pulse laser beam having profile 25 as shown in Fig. 20(d) is applied. In this occasion, the second pulse laser beam is applied to a position such that profile 25 overlaps the gradient portion of profile 24 on the rear side in the direction in which object 9 moves, that is, on the side opposite to arrow 71. As a result, as shown in Fig. 20(e), melted portion 26 is formed in the region covered with profile 25. In this occasion, a laterally growing crystal 31 on the front side in the direction in which object 9 moves remains, whereas laterally growing crystal 31 on the rear side in the direction in which object 9 moves becomes melted portion 26 again. As object 9 in this state is cooled, the portion which was melted portion 26 becomes amorphous as shown in Fig. 20(f) to be an amorphous portion 37. Next, the first pulse laser beam having a profile 24n as shown in Fig. 20(g) is applied. Profile 24n is displaced to the right in the drawing as compared with profile 24 when the first pulse laser beam was applied previously. Accordingly, as shown in Fig. 20(h), laterally growing crystal 31 on the left side in the drawing remains, and amorphous portion 37 becomes melted portion 26 again. In this occasion, the gradient portion of profile 24n is at a position displaced to the right in the drawing as compared to the gradient portion formed in profile 24, and thus the crystal further grows from an end portion of laterally growing crystal 31 to the right side in the drawing. Therefore, an elongated, excellent quality crystal as a laterally growing crystal 38 shown in Fig. 20(i) is formed after cooling. Although laterally growing crystal 31 is also formed at

the gradient portion of profile 24 on the right side in the drawing, this portion later becomes amorphous by being irradiated with the second pulse laser beam in the ultraviolet range having profile 25 (see Fig. 20(d)) again. Scanning on the surface of object 9 proceeds as the cycle from Fig. ~~20(a)~~ 20(d) to Fig. 20(i) is repeated according to such procedures.